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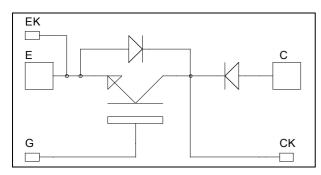


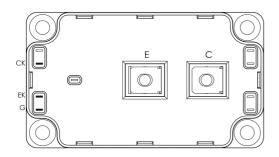


Single switch with Series diode Trench + Field Stop IGBT4

$$V_{CES} = 1200V$$

 $I_{C} = 475A$ @ $T_{C} = 100$ °C





Application

• Zero Current Switching resonant mode

Feature

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
$I_{\rm C}$	Continuous Collector Current	$T_c = 25$ °C	610	
	Continuous Conector Current	$T_{c} = 100^{\circ}C$	475	A
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	800	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	2307	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	800A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$; $V_{CE} = 1200V$				4	mA
$V_{\text{CE(sat)}}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 400A$	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		1.8	2.2	V
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 10 \text{ mA}$		5	5.8	6.5	V

Dynamic Characteristics

Symbol	Characteristic	Test Conditions			Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			24.6		nF
Coes	Output Capacitance				1.62		
C_{res}	Reverse Transfer Capacitance				1.38		
Q_{G}	Gate charge	V _{GE} =±15V			3.4		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switc	thing (25°C)		160		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			30		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 400A$		340		ns	
T_{f}	Fall Time	$R_G = 1.8\Omega$		80			
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C)				
$T_{\rm r}$	Rise Time		$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 400A$ $R_{G} = 1.8\Omega$		40		ns
$T_{d(off)}$	Turn-off Delay Time				450		
$T_{\rm f}$	Fall Time	$R_G = 1.8\Omega$			170		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25$ °C		20.8		mJ
Lon		$V_{CE} = 600V$			42		1113
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 400 A$	$T_J = 25^{\circ}C$		22		mJ
LOII		$R_G = 1.8\Omega$	$R_{\rm G} = 1.8\Omega \qquad T_{\rm J} = 150^{\circ}{\rm C}$		37.2		1113
I_{SC}	Short circuit current		$V_{GE} \le 15V ; V_{CC} = 900V$ $t_p \le 10 \mu s ; T_j = 150 ^{\circ} C$		2000		A

Series diode ratings and characteristics

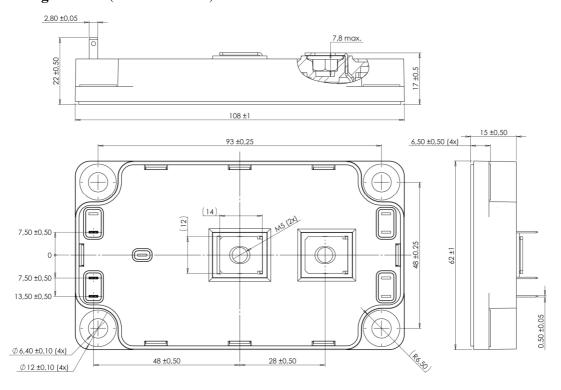
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$			400 2000	μА
I_{F}	DC Forward Current		$T_j = 123 \text{ C}$ $T_j = 90 \text{ C}$		360	2000	A
	Diode Forward Voltage	$I_F = 360A$	= 360A		2.5	3	
V_{F}		$I_F = 720A$			3		V
		$I_F = 360A$	$T_{j} = 125^{\circ}C$		1.8		
t _{rr}	Reverse Recovery Time		$T_j = 25$ °C		265		ns
		$I_F = 360A$ $V_R = 800V$	$T_{j} = 125^{\circ}C$		350		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 1200A/\mu s$	$T_j = 25$ °C		3.3		μC
			$T_{j} = 125^{\circ}C$		17.3		μС



Thermal and package characteristics

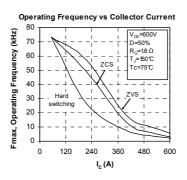
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.065	°C/W
IX _{th} JC			Series diode			0.13	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	°C
T_{STG}	Storage Temperature Range			-40		125	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M6	3		5	N.m
		For teminals	M5	2		3.5	18.111
Wt	Package Weight					300	gg

SP6 Package outline (dimensions in mm)

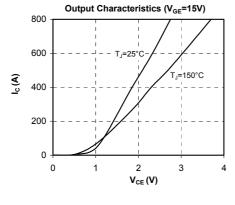


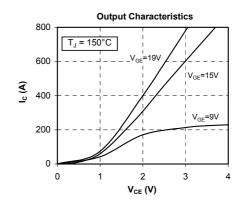
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

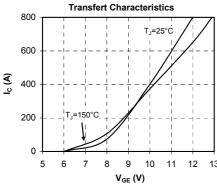
Typical IGBT Performance Curve

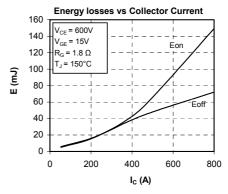


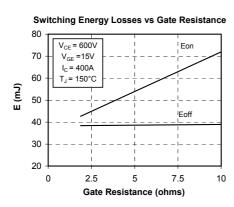


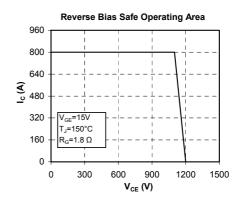


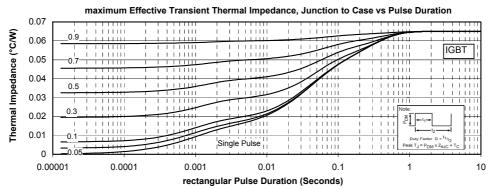






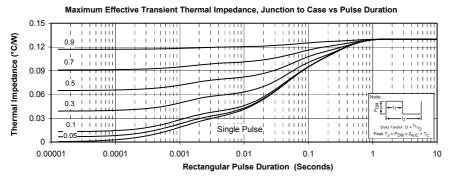


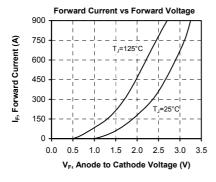


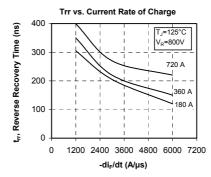


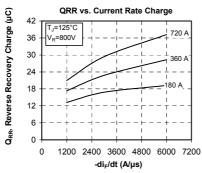


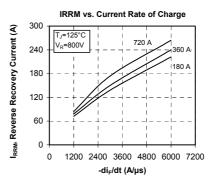
Typical Series diode Performance Curve

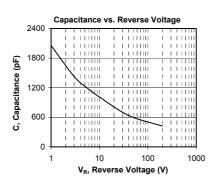


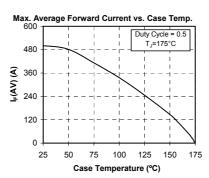












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